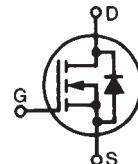


PolarHT™ Power MOSFET

IXTQ 96N15P IXTT 96N15P

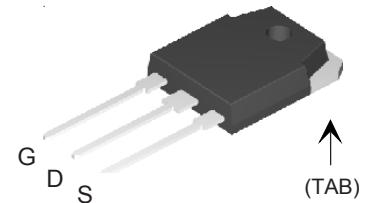
V_{DSS}	=	150	V
I_{D25}	=	96	A
$R_{DS(on)}$	\leq	24	$m\Omega$

N-Channel Enhancement Mode
Avalanche Rated

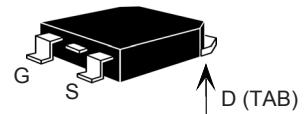


Symbol	Test Conditions	Maximum Ratings		
V_{DSS}	$T_J = 25^\circ C$ to $150^\circ C$	150	V	
V_{DGR}	$T_J = 25^\circ C$ to $150^\circ C$; $R_{GS} = 1 M\Omega$	150	V	
V_{GSS}	Continuous	± 20	V	
V_{GSM}	Transient	± 30	V	
I_{D25}	$T_c = 25^\circ C$	96	A	
$I_{D(RMS)}$	External lead current limit	75	A	
I_{DM}	$T_c = 25^\circ C$, pulse width limited by T_{JM}	250	A	
I_{AR}	$T_c = 25^\circ C$	60	A	
E_{AR}	$T_c = 25^\circ C$	40	mJ	
E_{AS}	$T_c = 25^\circ C$	1.0	J	
dv/dt	$I_s \leq I_{DM}$, $di/dt \leq 100 A/\mu s$, $V_{DD} \leq V_{DSS}$ $T_j \leq 150^\circ C$, $R_G = 4 \Omega$	10	V/ns	
P_D	$T_c = 25^\circ C$	480	W	
T_J		-55 ... +175	$^\circ C$	
T_{JM}		175	$^\circ C$	
T_{stg}		-55 ... +150	$^\circ C$	
T_L	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ C$	
T_{SOLD}	Plastic body for 10 s	260	$^\circ C$	
M_d	Mounting torque (TO-3P)	1.13/10	Nm/lb.in.	
Weight	TO-3P	5.5	g	
	TO-268	5.0	g	

TO-3P (IXTQ)



TO-268 (IXTT)



G = Gate D = Drain
S = Source TAB = Drain

Features

- International standard packages
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
 - easy to drive and to protect

Advantages

- Easy to mount
- Space savings
- High power density

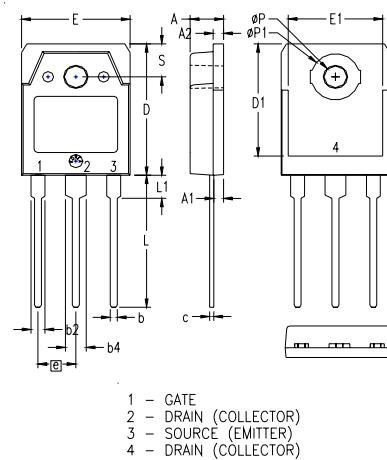
Symbol	Test Conditions	Characteristic Values		
	($T_j = 25^\circ C$, unless otherwise specified)	Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0 V$, $I_D = 250 \mu A$	150		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	2.5		5.0 V
I_{GSS}	$V_{GS} = \pm 20 V_{DC}$, $V_{DS} = 0$		± 100	nA
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0 V$	$T_j = 125^\circ C$	25	μA
			250	μA
$R_{DS(on)}$	$V_{GS} = 10 V$, $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300 \mu s$, duty cycle $d \leq 2 \%$		24	$m\Omega$

Symbol **Test Conditions**
Characteristic Values
 $(T_J = 25^\circ C, \text{ unless otherwise specified})$
Min. **Typ.** **Max.**

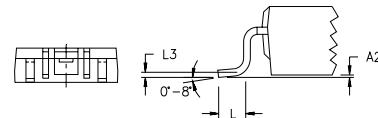
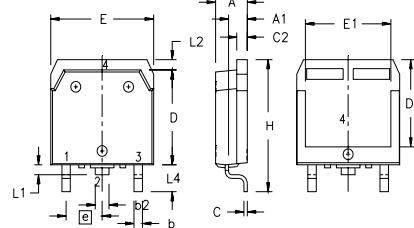
g_{fs}	$V_{DS} = 10 V; I_D = 0.5 I_{D25}$, pulse test	35	45	S
C_{iss} C_{oss} C_{rss}	$V_{GS} = 0 V, V_{DS} = 25 V, f = 1 \text{ MHz}$	3500	pF	
		1000	pF	
		280	pF	
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	$V_{GS} = 10 V, V_{DS} = 0.5 V_{DSS}, I_D = 60 A$ $R_G = 4 \Omega$ (External)	30	ns	
		33	ns	
		66	ns	
		18	ns	
$Q_{g(on)}$ Q_{gs} Q_{gd}	$V_{GS} = 10 V, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$	110	nC	
		26	nC	
		59	nC	
R_{thJC}			0.31	$^\circ C/W$
R_{thcs}	(TO-3P)	0.21		$^\circ C/W$

Source-Drain Diode
Characteristic Values
 $(T_J = 25^\circ C, \text{ unless otherwise specified})$

Symbol	Test Conditions	Min.	Typ.	Max.
I_s	$V_{GS} = 0 V$			96 A
I_{SM}	Repetitive			250 A
V_{SD}	$I_F = I_s, V_{GS} = 0 V,$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2 \%$		1.5	V
t_{rr} Q_{RM}	$I_F = 25 A, -di/dt = 100 A/\mu\text{s}$	150	ns	
	$V_R = 100 V, V_{GS} = 0 V$	2.0		μC

TO-3P (IXTQ) Outline

 1 - GATE
 2 - DRAIN (COLLECTOR)
 3 - SOURCE (EMITTER)
 4 - DRAIN (COLLECTOR)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.193	4.70	4.90
A1	.051	.059	1.30	1.50
A2	.057	.065	1.45	1.65
b	.035	.045	0.90	1.15
b2	.075	.087	1.90	2.20
b4	.114	.126	2.90	3.20
c	.022	.031	0.55	0.80
D	.780	.799	19.80	20.30
D1	.665	.677	16.90	17.20
E	.610	.622	15.50	15.80
E1	.531	.539	13.50	13.70
e	.215 BSC		5.45 BSC	
L	.779	.795	19.80	20.20
L1	.134	.142	3.40	3.60
ϕP	.126	.134	3.20	3.40
$\phi P1$.272	.280	6.90	7.10
S	.193	.201	4.90	5.10

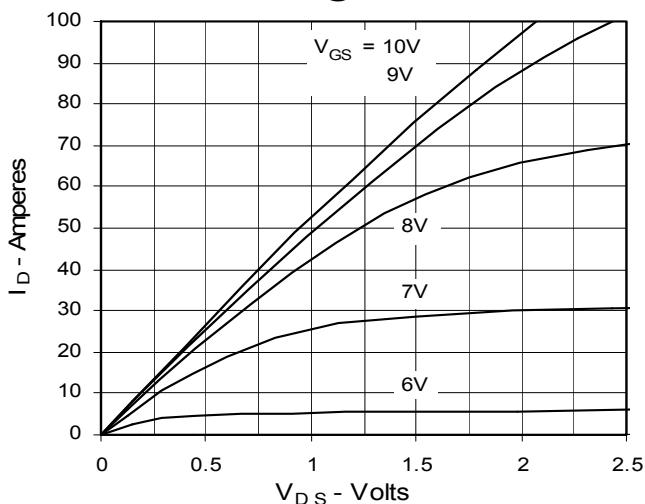
TO-268 (IXTT) Outline


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

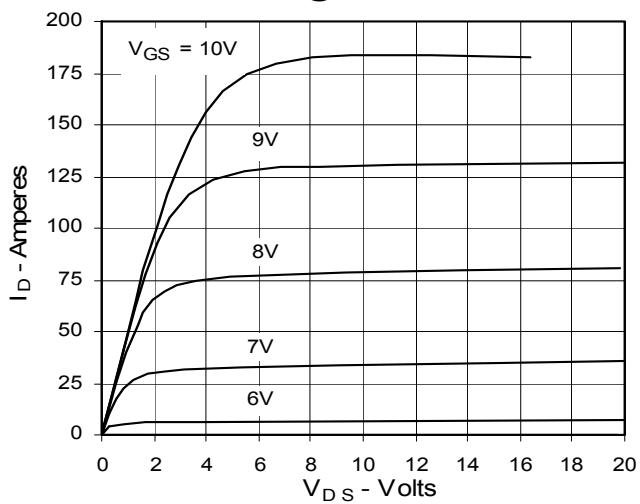
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**Fig. 1. Output Characteristics
@ 25°C**



**Fig. 2. Extended Output Characteristics
@ 25°C**



**Fig. 3. Output Characteristics
@ 150°C**

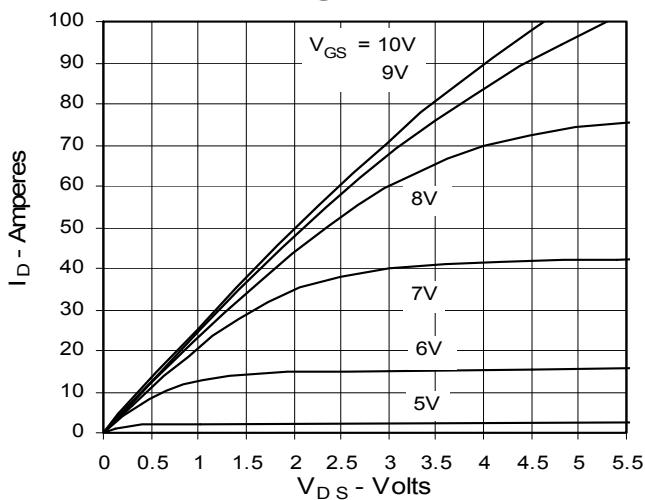
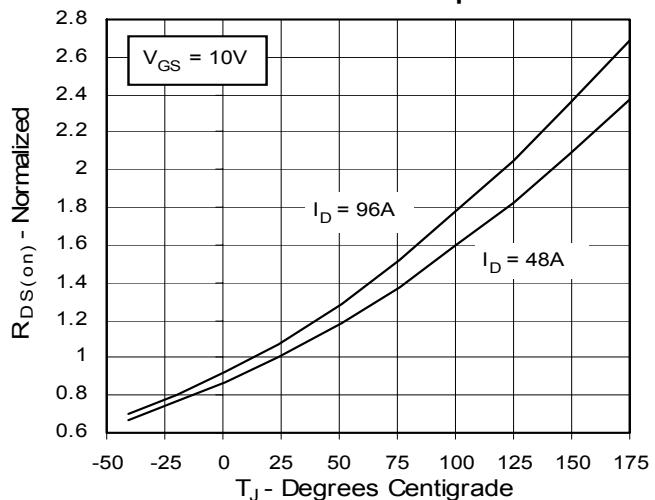
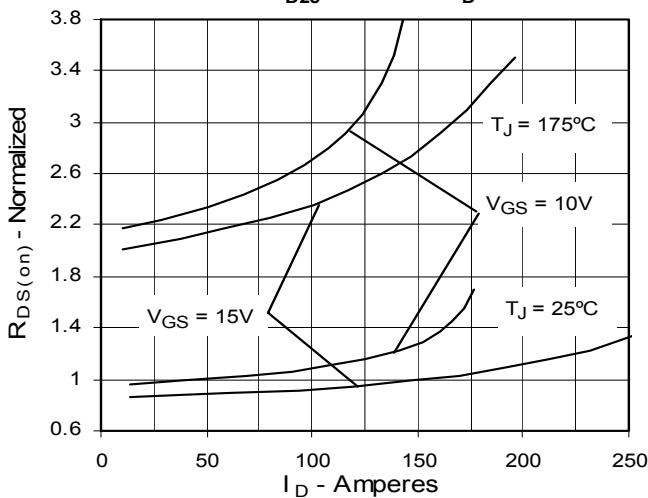


Fig. 4. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. Junction Temperature



**Fig. 5. $R_{DS(on)}$ Normalized to
0.5 I_{D25} Value vs. I_D**



**Fig. 6. Drain Current vs. Case
Temperature**

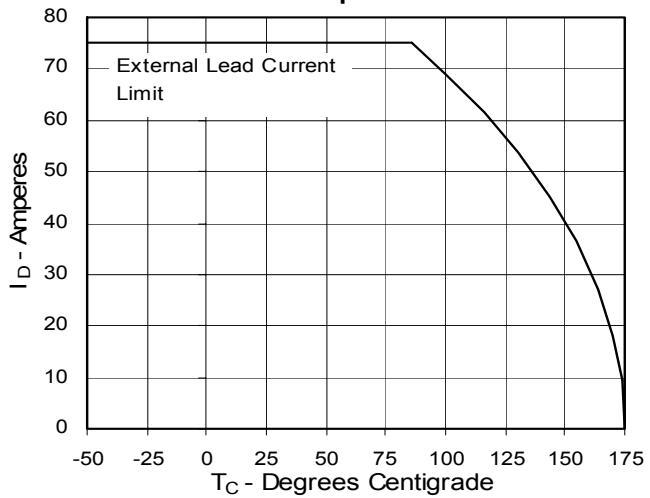


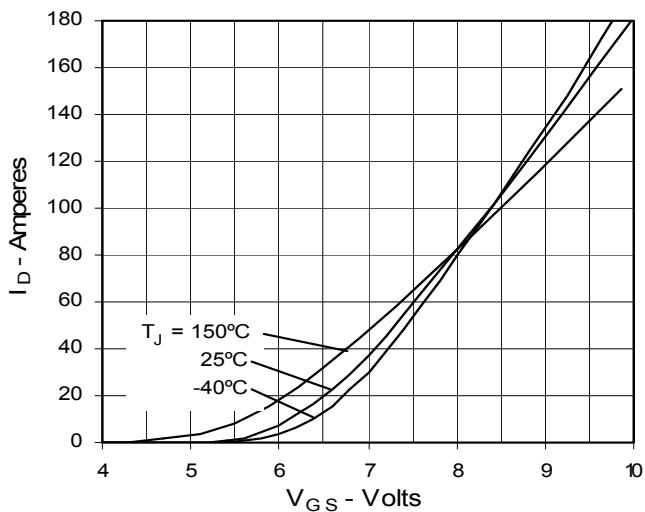
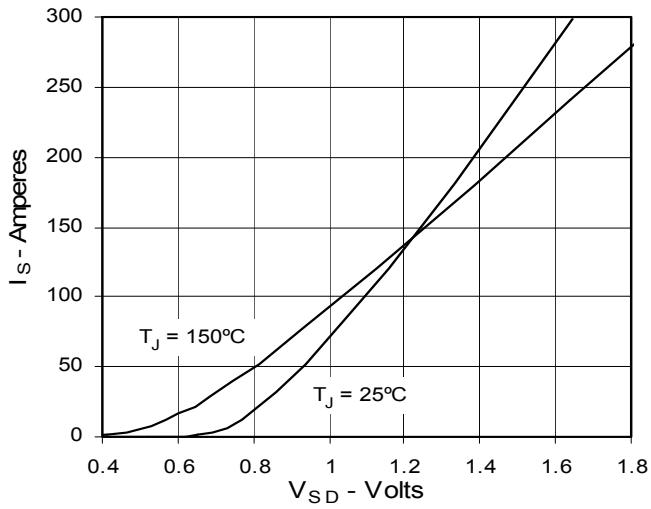
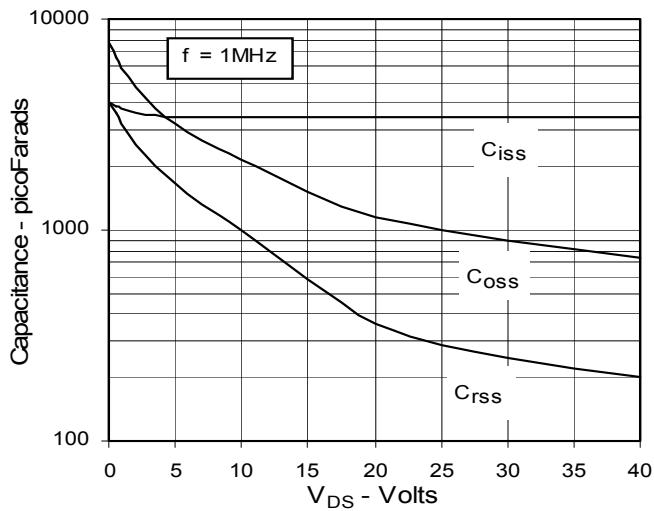
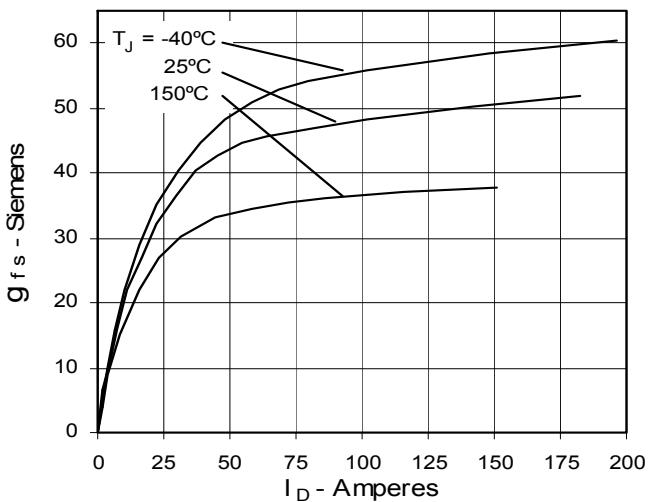
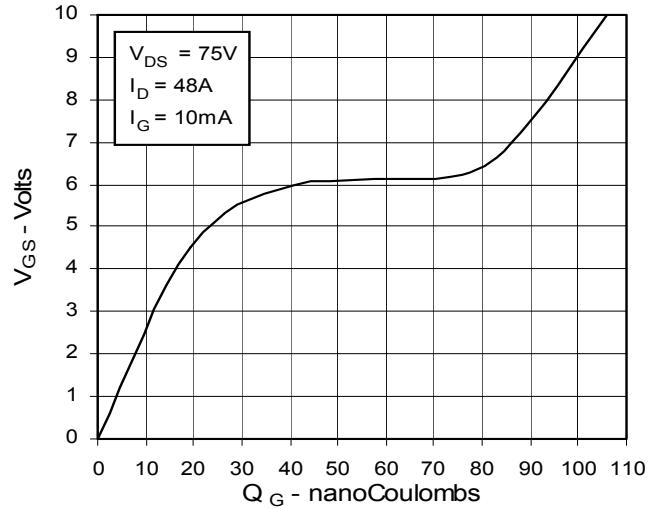
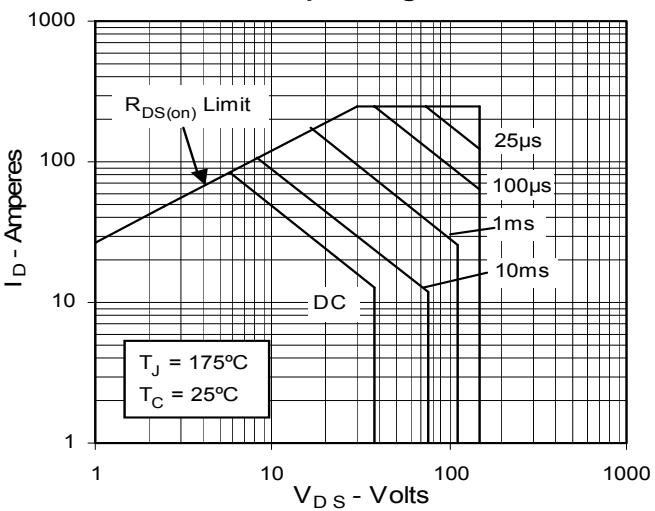
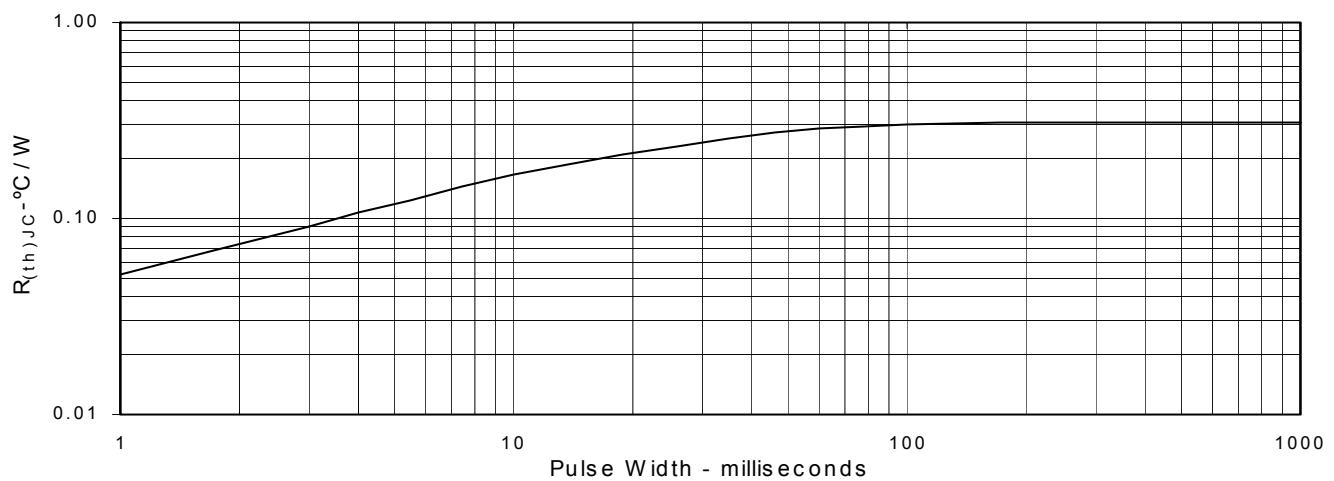
Fig. 7. Input Admittance

**Fig. 9. Source Current vs.
Source-To-Drain Voltage**

Fig. 11. Capacitance

Fig. 8. Transconductance

Fig. 10. Gate Charge

**Fig. 12. Forward-Bias
Safe Operating Area**


Fig. 13. Maximum Transient Thermal Resistance



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